

Randall Feenstra

List of Publications by Year in descending order

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269
papers

14,867
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16451

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9425
citing authors

#	ARTICLE	IF	CITATIONS
1	Acquisition and analysis of scanning tunneling spectroscopy data of WSe ₂ monolayer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	5
2	Unexplored MBE growth mode reveals new properties of superconducting NbN. Physical Review Materials, 2021, 5, .	2.4	10
3	Photophysics and Electronic Structure of Lateral Graphene/MoS ₂ and Metal/MoS ₂ Junctions. ACS Nano, 2020, 14, 16663-16671.	14.6	11
4	Flat Bands and Mechanical Deformation Effects in the Moiré Superlattice of MoS ₂ -WSe ₂ Heterobilayers. ACS Nano, 2020, 14, 7564-7573.	14.6	38
5	Proximity-induced superconducting gap in the quantum spin Hall edge state of monolayer WTe ₂ . Nature Physics, 2020, 16, 526-530.	16.7	76
6	WSe ₂ homojunctions and quantum dots created by patterned hydrogenation of epitaxial graphene substrates. 2D Materials, 2019, 6, 021001.	4.4	7
7	Formation of graphene atop a Si adlayer on the C-face of SiC. Physical Review Materials, 2019, 3, .	2.4	3
8	One dimensional metallic edges in atomically thin WSe ₂ induced by air exposure. 2D Materials, 2018, 5, 025017.	4.4	47
9	Magnitude of the current in 2D interlayer tunneling devices. Journal of Physics Condensed Matter, 2018, 30, 055703.	1.8	2
10	Quantum-Confined Electronic States Arising from the Moiré Pattern of MoS ₂ -WSe ₂ Heterobilayers. Nano Letters, 2018, 18, 1849-1855.	9.1	91
11	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. ACS Nano, 2018, 12, 965-975.	14.6	172
12	Large scale 2D/3D hybrids based on gallium nitride and transition metal dichalcogenides. Nanoscale, 2018, 10, 336-341.	5.6	38
13	Substitutional mechanism for growth of hexagonal boron nitride on epitaxial graphene. Applied Physics Letters, 2018, 113, .	3.3	6
14	Characterization of hexagonal boron nitride layers on nickel surfaces by low-energy electron microscopy. Surface Science, 2017, 659, 31-42.	1.9	20
15	Carbon-assisted chemical vapor deposition of hexagonal boron nitride. 2D Materials, 2017, 4, 025117.	4.4	54
16	Epitaxial graphene homogeneity and quantum Hall effect in millimeter-scale devices. Carbon, 2017, 115, 229-236.	10.3	57
17	Characteristics of Interlayer Tunneling Field-Effect Transistors Computed by a DFT-Bardeen Method. Journal of Electronic Materials, 2017, 46, 1378-1389.	2.2	5
18	Properties of synthetic epitaxial graphene/molybdenum disulfide lateral heterostructures. Carbon, 2017, 125, 551-556.	10.3	27

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19	Growth and electronic properties of nanolines on TiO ₂ -terminated SrTiO ₃ (001) surfaces. Journal of Applied Physics, 2017, 122, 124305.	2.5	1
20	Thickness characterization of atomically thin WSe ₂ on epitaxial graphene by low-energy electron reflectivity oscillations. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	1.2	10
21	Formation of hexagonal boron nitride on graphene-covered copper surfaces. Journal of Materials Research, 2016, 31, 945-958.	2.6	17
22	Tuning electronic transport in epitaxial graphene-based van der Waals heterostructures. Nanoscale, 2016, 8, 8947-8954.	5.6	21
23	Chemically selective formation of Si ³⁺ on SiGe(110) and (001) for ALD nucleation using H ₂ O ₂ (g). Surface Science, 2016, 652, 322-333.	1.9	7
24	Scanning Tunneling Microscopy and Spectroscopy of Air Exposure Effects on Molecular Beam Epitaxy Grown WSe ₂ Monolayers and Bilayers. ACS Nano, 2016, 10, 4258-4267.	14.6	72
25	Oxygen vacancies on SrO-terminated SrTiO ₃ studied by scanning tunneling spectroscopy. Physical Review B, 2015, 91, .	3.2	22
26	Theory of resonant tunneling in bilayer-graphene/hexagonal-boron-nitride heterostructures. Applied Physics Letters, 2015, 106, .	3.3	23
27	Comprehensive structural and optical characterization of MBE grown MoSe ₂ on graphite, CaF ₂ and graphene. 2D Materials, 2015, 2, 024007.	4.4	120
28	Probing Critical Point Energies of Transition Metal Dichalcogenides: Surprising Indirect Gap of Single Layer WSe ₂ . Nano Letters, 2015, 15, 6494-6500.	9.1	175
29	Electronic states of two-dimensional materials and heterostructures. , 2015, , .		0
30	Topographic and electronic structure of cleaved SrTiO ₃ (001) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	6
31	Inelastic effects in low-energy electron reflectivity of two-dimensional materials. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 02B105.	1.2	7
32	2.2.8 Ni, Nickel. , 2015, , 36-37.		0
33	2.3.2 AlN, Aluminum Nitride. , 2015, , 46-46.		0
34	2.3.15 SiC, Silicon Carbide. , 2015, , 65-66.		0
35	2.3.14 Si, Silicon. , 2015, , 62-64.		0
36	Energy Gap Induced by Friedel Oscillations Manifested as Transport Asymmetry at Monolayer-Bilayer Graphene Boundaries. Physical Review X, 2014, 4, .	8.9	39

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37	Formation of a Buffer Layer for Graphene on C-Face SiC{0001}. Journal of Electronic Materials, 2014, 43, 819-827.	2.2	4
38	Tunneling characteristics in chemical vapor deposited graphene-hexagonal boron nitride-graphene junctions. Applied Physics Letters, 2014, 104, .	3.3	49
39	Theory of graphene-insulator-graphene tunnel junctions. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	1.2	36
40	Hot carriers in epitaxial graphene sheets with and without hydrogen intercalation: role of substrate coupling. Nanoscale, 2014, 6, 10562-10568.	5.6	4
41	Spatially Resolved Mapping of Electrical Conductivity across Individual Domain (Grain) Boundaries in Graphene. ACS Nano, 2013, 7, 7956-7966.	14.6	124
42	Graphene Nucleation Density on Copper: Fundamental Role of Background Pressure. Journal of Physical Chemistry C, 2013, 117, 18919-18926.	3.1	179
43	Low-energy electron reflectivity of graphene on copper and other substrates. Physical Review B, 2013, 87, .	3.2	43
44	Low-energy electron reflectivity from graphene: First-principles computations and approximate models. Ultramicroscopy, 2013, 130, 101-108.	1.9	24
45	SymFET: A Proposed Symmetric Graphene Tunneling Field-Effect Transistor. IEEE Transactions on Electron Devices, 2013, 60, 951-957.	3.0	93
46	Atomic-Scale Mapping of Thermoelectric Power on Graphene: Role of Defects and Boundaries. Nano Letters, 2013, 13, 3269-3273.	9.1	52
47	Low-energy electron reflectivity from graphene. Physical Review B, 2013, 87, .	3.2	83
48	Formation of graphene on SiC(0001) surfaces in disilane and neon environments. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 04E102.	1.2	2
49	Interface structure of graphene on SiC(0001) surfaces in disilane and neon environments. Physical Review B, 2012, 85, .	3.2	27
50	Charge transfer between isomer domains on n+-doped Si(111)-2x1: energetic stabilization. Journal of Physics Condensed Matter, 2012, 24, 354009.	1.8	5
51	Single-particle tunneling in doped graphene-insulator-graphene junctions. Journal of Applied Physics, 2012, 111, .	2.5	144
52	Structure and electronic spectroscopy of steps on GaAs(110) surfaces. Surface Science, 2012, 606, 28-33.	1.9	17
53	Graphene formed on SiC under various environments: comparison of Si-face and C-face. Journal Physics D: Applied Physics, 2012, 45, 154001.	2.8	44
54	Evidences of electrochemical graphene functionalization and substrate dependence by Raman and scanning tunneling spectroscopies. Journal of Applied Physics, 2012, 111, 114306.	2.5	22

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55	Quantitative Determination of Nanoscale Electronic Properties of Semiconductor Surfaces by Scanning Tunnelling Spectroscopy. Journal of Physics: Conference Series, 2011, 326, 012009.	0.4	4
56	Coexistence of Negatively and Positively Buckled Isomers on n-Doped Si(111). Physical Review Letters, 2011, 106, 067601.	7.8	27
57	Formation of epitaxial graphene on SiC(0001) using vacuum or argon environments. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C5C1-C5C7.	1.2	26
58	Electronic states of InAs/GaAs quantum dots by scanning tunneling spectroscopy. Applied Physics Letters, 2010, 97, 123110.	3.3	11
59	Thickness monitoring of graphene on SiC using low-energy electron diffraction. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 958-962.	2.1	13
60	Size, shape, composition, and electronic properties of InAs/GaAs quantum dots by scanning tunneling microscopy and spectroscopy. Journal of Applied Physics, 2010, 108, 114315.	2.5	32
61	Ultrafast Transient Absorption Microscopy Studies of Carrier Dynamics in Epitaxial Graphene. Nano Letters, 2010, 10, 1308-1313.	9.1	164
62	Comparison of graphene formation on C-face and Si-face SiC {0001} surfaces. Physical Review B, 2010, 82, .	3.2	76
63	Gigahertz operation of epitaxial graphene transistors. , 2009, , .		0
64	Contrast mechanisms in cross-sectional scanning tunneling microscopy of GaSb/GaAs type-II nanostructures. Journal of Applied Physics, 2009, 105, .	2.5	14
65	Influence of surface states on tunneling spectra of n-type GaAs(110) surfaces. Physical Review B, 2009, 80, .	3.2	37
66	Morphology of graphene on SiC(0001) surfaces. Applied Physics Letters, 2009, 95, 073101.	3.3	33
67	Temperature Dependence of Epitaxial Graphene Formation on SiC(0001). Journal of Electronic Materials, 2009, 38, 718-724.	2.2	35
68	The influence of the band structure of epitaxial graphene on SiC on the transistor characteristics. Solid State Communications, 2009, 149, 2194-2198.	1.9	8
69	A prospective: Quantitative scanning tunneling spectroscopy of semiconductor surfaces. Surface Science, 2009, 603, 2841-2844.	1.9	21
70	Tunneling spectroscopy of graphene and related reconstructions on SiC(0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1052-1057.	2.1	21
71	Molecular dynamics and first-principles computations of Ga adlayers on GaN(0001). Physica Status Solidi (B): Basic Research, 2008, 245, 920-923.	1.5	7
72	Step formation on hydrogen-etched 6H-SiC{0001} surfaces. Surface Science, 2008, 602, 2936-2942.	1.9	44

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73	Growth of nanoscale BaTiO ₃ /SrTiO ₃ superlattices by molecular-beam epitaxy. <i>Journal of Materials Research</i> , 2008, 23, 1417-1432.	2.6	49
74	Nucleation and Stoichiometry Dependence of Rutile-TiO ₂ (001)/GaN(0001) Thin Films Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1108, 1.	0.1	0
75	Electronic states of chemically treated SiC surfaces. <i>Journal of Applied Physics</i> , 2008, 103, 013709.	2.5	8
76	Band offsets of InGaAs heterojunctions by scanning tunneling spectroscopy. <i>Journal of Applied Physics</i> , 2008, 103, 073704.	2.5	31
77	Influence of tip-induced band bending on tunnelling spectra of semiconductor surfaces. <i>Nanotechnology</i> , 2007, 18, 044015.	2.6	89
78	Field effect in epitaxial graphene on a silicon carbide substrate. <i>Applied Physics Letters</i> , 2007, 90, 253507.	3.3	132
79	A study of the morphology of GaN seed layers on in situ deposited SixNy and its effect on properties of overgrown GaN epilayers. <i>Journal of Crystal Growth</i> , 2006, 291, 301-308.	1.5	12
80	Band gap of the Ge(111)c(2 \times 8) surface by scanning tunneling spectroscopy. <i>Physical Review B</i> , 2006, 73, .	3.2	78
81	Electronic states of oxidized GaN(0001) surfaces. <i>Applied Physics Letters</i> , 2006, 89, 171920.	3.3	26
82	Oxidized GaN(0001) surfaces studied by scanning tunneling microscopy and spectroscopy and by first-principles theory. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 2080.	1.3	43
83	Effects of hydrogen during molecular beam epitaxy of GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2183-2186.	0.8	2
84	Dislocation density reduction in GaN using porous SiN interlayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 722-726.	1.8	31
85	Recent developments in surface studies of GaN and AlN. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 1174.	1.6	65
86	InGaAsInP quantum well intermixing studied by high-resolution x-ray diffraction and grazing incidence x-ray analysis. <i>Journal of Applied Physics</i> , 2005, 97, 093519.	2.5	3
87	Effects of hydrogen on the morphology and electrical properties of GaN grown by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005, 86, 121914.	3.3	11
88	Efficacy of single and double SiNx interlayers on defect reduction in GaN overlayers grown by organometallic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , 2005, 98, 123502.	2.5	26
89	Low-temperature tunneling spectroscopy of Ge(111)c(2 \times 8) surfaces. <i>Physical Review B</i> , 2005, 71, .	3.2	64
90	Transport limitations in tunneling spectroscopy of Ge(111)c(2 \times 8) surfaces. <i>Physical Review B</i> , 2004, 69, .	3.2	30

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91	Cross-sectional scanning tunneling microscopy and spectroscopy of InGaP/GaAs heterojunctions. Applied Physics Letters, 2004, 84, 227-229.	3.3	19
92	Buckling of Si and Ge(111)2Å-1 surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1671-1674.	2.1	16
93	Growth of GaN on porous SiC and GaN substrates. Journal of Electronic Materials, 2003, 32, 855-860.	2.2	51
94	Low energy electron microscopy of indium on Si(001) surfaces. Surface Science, 2003, 547, 127-138.	1.9	8
95	Growth of GaN on porous SiC and GaN substrates. Physica Status Solidi A, 2003, 200, 44-47.	1.7	6
96	In-situ ellipsometry: Identification of surface terminations during GaN growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2938-2943.	0.8	4
97	Cross-sectional scanning tunneling microscopy studies of lattice-matched InGaAs/InP quantum wells: variations in growth switching sequence. Journal of Crystal Growth, 2003, 249, 437-444.	1.5	9
98	Reconstructions of the AlN(0001) surface. Physical Review B, 2003, 68, .	3.2	70
99	Adatom Kinetics On and Below the Surface: The Existence of a New Diffusion Channel. Physical Review Letters, 2003, 90, 056101.	7.8	293
100	Growth and Surface Reconstructions of AlN(0001) Films. Materials Research Society Symposia Proceedings, 2003, 798, 383.	0.1	0
101	Combined MOCVD and MBE growth of GaN on porous SiC. Materials Research Society Symposia Proceedings, 2003, 798, 760.	0.1	4
102	Morphology and surface reconstructions of GaN(111,00) surfaces. Applied Physics Letters, 2003, 82, 1793-1795.	3.3	35
103	Surface termination during GaN growth by metalorganic vapor phase epitaxy determined by ellipsometry. Journal of Applied Physics, 2003, 94, 6997-6999.	2.5	17
104	Electrostatic potential for a hyperbolic probe tip near a semiconductor. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 2080.	1.6	123
105	Scanning tunneling microscopy images of III-V semiconductor alloys: Strain effects. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 18.	1.6	9
106	Plasma-assisted molecular beam epitaxy of GaN on porous SiC substrates with varying porosity. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1812.	1.6	25
107	Low-temperature scanning tunneling spectroscopy of n-type GaAs(110) surfaces. Physical Review B, 2002, 66, .	3.2	50
108	Morphology and effects of hydrogen etching of porous SiC. Journal of Applied Physics, 2002, 92, 4070-4074.	2.5	45

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109	Scanning tunneling potentiometry of semiconductor junctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1677.	1.6	21
110	Morphology and surface reconstructions of m-plane GaN. Materials Research Society Symposia Proceedings, 2002, 743, L4.1.1.	0.1	2
111	Structural Properties of GaN Films Grown by Molecular Beam Epitaxy on Singular and Vicinal 6H-SiC(0001). MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	13
112	Review of Structure of Bare and Adsorbate-Covered GaN(0001) Surfaces. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	62
113	Growth of Gan on Porous Sic Substrates by Plasma-Assisted Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2002, 722, 131.	0.1	18
114	Adsorption and incorporation of silicon at GaN(0001) surfaces. Applied Physics Letters, 2002, 80, 2008-2010.	3.3	57
115	Structural Properties of GaN films grown by Molecular Beam Epitaxy on vicinal SiC(0001). Materials Research Society Symposia Proceedings, 2001, 693, 471.	0.1	3
116	Indium incorporation and surface segregation during InGaN growth by molecular beam epitaxy: experiment and theory. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	46
117	Recent developments in scanning tunneling spectroscopy of semiconductor surfaces. Applied Physics A: Materials Science and Processing, 2001, 72, S193-S199.	2.3	7
118	Properties of GaN epitaxial layers grown on 6H-SiC(0001) by plasma-assisted molecular beam epitaxy. Journal of Electronic Materials, 2001, 30, 162-169.	2.2	34
119	Growth of GaN on SiC(0001) by Molecular Beam Epitaxy. Physica Status Solidi A, 2001, 188, 595-599.	1.7	10
120	Distribution of nitrogen atoms in dilute GaAsN and InGaAsN alloys studied by scanning tunneling microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1644.	1.6	23
121	Silicon on GaN(0001) and (0001 $\bar{1}$,) surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1619.	1.6	8
122	Arrangement of nitrogen atoms in GaAsN alloys determined by scanning tunneling microscopy. Applied Physics Letters, 2001, 78, 82-84.	3.3	44
123	Buckling and band gap of the Ge(111)2 $\bar{1}$ —1 surface studied by low-temperature scanning tunneling microscopy. Physical Review B, 2001, 64, .	3.2	25
124	Role of Ga flux in dislocation reduction in GaN films grown on SiC(0001). Applied Physics Letters, 2001, 79, 3428-3430.	3.3	59
125	InGaAs/InP quantum well intermixing studied by cross-sectional scanning tunneling microscopy. Journal of Applied Physics, 2001, 89, 4815-4823.	2.5	32
126	Structure of clean and arsenic-covered GaN(0001) surfaces. Journal of Crystal Growth, 2000, 209, 355-363.	1.5	47

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127	Reconstructions of GaN and InGaN surfaces. Applied Surface Science, 2000, 166, 165-172.	6.1	20
128	Surface activity of magnesium during GaN molecular beam epitaxial growth. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 280-286.	1.0	2
129	SURFACE MORPHOLOGY OF GaN SURFACES DURING MOLECULAR BEAM EPITAXY. Surface Review and Letters, 2000, 07, 601-606.	1.1	17
130	Surface structures and growth kinetics of InGaN(0001) grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2284.	1.6	72
131	Optimized structural properties of wurtzite GaN on SiC(0001) grown by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1915-1918.	2.1	21
132	Comment on "Structures of GaN(0001) $\sqrt{2}\times\sqrt{2}$, $\sqrt{4}\times\sqrt{4}$, and $\sqrt{5}\times\sqrt{5}$ Surface Reconstructions". Physical Review Letters, 2000, 84, 4014-4014.	7.8	16
133	Structure of GaN(0001): The laterally contracted Ga bilayer model. Physical Review B, 2000, 61, 9932-9935.	3.2	322
134	Spontaneous Formation of Indium-Rich Nanostructures on InGaN(0001) Surfaces. Physical Review Letters, 2000, 85, 1902-1905.	7.8	95
135	Indium incorporation and surface segregation during InGaN growth by molecular beam epitaxy. Materials Research Society Symposia Proceedings, 2000, 639, 261.	0.1	0
136	Surface Morphology of GaN Surfaces During Molecular Beam Epitaxy. Surface Review and Letters, 2000, 7, 601-606.	1.1	1
137	TEM Study of the Morphology Of GaN/SiC (0001) Grown at Various Temperatures by MBE. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 238-244.	1.0	1
138	Scanning Tunneling Spectroscopy of Mott-Hubbard States on the 6H-SiC(0001) $\sqrt{3}\times\sqrt{3}$ Surface. Physical Review Letters, 1999, 82, 1000-1003.	7.8	108
139	Compositional variations in strain-compensated InGaAsP/InAsP superlattices studied by scanning tunneling microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 2251-2256.	2.1	5
140	Temperature dependence of molecular beam epitaxy of GaN on SiC (0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1289-1293.	2.1	32
141	Tunneling spectroscopy of the Si(111) 2×1 surface. Physical Review B, 1999, 60, 4478-4480.	3.2	13
142	Inversion of wurtzite GaN(0001) by exposure to magnesium. Applied Physics Letters, 1999, 75, 808-810.	3.3	187
143	Comparison of electronic and mechanical contrast in scanning tunneling microscopy images of semiconductor heterojunctions. Physica B: Condensed Matter, 1999, 273-274, 796-802.	2.7	51
144	Enhanced group-V intermixing in InGaAs/InP quantum wells studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 1999, 75, 79-81.	3.3	39

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145	GaN(0001) surface structures studied using scanning tunneling microscopy and first-principles total energy calculations. <i>Surface Science</i> , 1999, 423, 70-84.	1.9	118
146	Scanning tunneling microscopy and spectroscopy of arsenic antisites in low temperature grown InGaAs. <i>Applied Physics Letters</i> , 1999, 74, 1439-1441.	3.3	63
147	TEM Study of the Morphology Of GaN/SiC (0001) Grown at Various Temperatures by MBE. <i>Materials Research Society Symposia Proceedings</i> , 1999, 595, 1.	0.1	0
148	Surface Activity of Magnesium During GaN Molecular Beam Epitaxial Growth. <i>Materials Research Society Symposia Proceedings</i> , 1999, 595, 1.	0.1	1
149	Scanning Tunneling Microscopy Studies of InGaN Growth by Molecular Beam Epitaxy. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999, 4, 858-863.	1.0	1
150	Scanning tunneling microscopy of the GaN(0001) surface. <i>Applied Physics A: Materials Science and Processing</i> , 1998, 66, S947-S951.	2.3	30
151	In situ real-time studies of GaN growth on 6H-SiC(0001) by low-energy electron microscopy (LEEM). <i>Journal of Crystal Growth</i> , 1998, 189-190, 310-316.	1.5	19
152	The search for residual resistivity dipoles by scanning tunneling potentiometry. <i>Superlattices and Microstructures</i> , 1998, 23, 699-709.	3.1	11
153	Preparation of atomically flat surfaces on silicon carbide using hydrogen etching. <i>Journal of Electronic Materials</i> , 1998, 27, 308-312.	2.2	188
154	Surface-Influenced Phase Separation in Organic Thin Films on Drying. <i>Langmuir</i> , 1998, 14, 483-489.	3.5	5
155	Effects of GaAs substrate misorientation on strain relaxation in In _x Ga _{1-x} As films and multilayers. <i>Journal of Applied Physics</i> , 1998, 83, 5137-5149.	2.5	102
156	Reconstructions of GaN(0001) and (0001 $\bar{1}$) surfaces: Ga-rich metallic structures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998, 16, 2242.	1.6	228
157	Determination of wurtzite GaN lattice polarity based on surface reconstruction. <i>Applied Physics Letters</i> , 1998, 72, 2114-2116.	3.3	305
158	Strain variations in InGaAsP/InGaP superlattices studied by scanning probe microscopy. <i>Applied Physics Letters</i> , 1998, 72, 1727-1729.	3.3	31
159	A comparison of spectroscopic and microscopic observations of ion-induced intermixing in InGaAs/InP quantum wells. <i>Applied Physics Letters</i> , 1998, 72, 1599-1601.	3.3	12
160	Wurtzite GaN surface structures studied by scanning tunneling microscopy and reflection high energy electron diffraction. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1998, 16, 1641-1645.	2.1	91
161	Scanning Tunneling Microscopy Studies of InGaN Growth by Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1998, 537, 1.	0.1	0
162	Selective Intermixing of Ion Irradiated Semiconductor Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 1998, 540, 15.	0.1	2

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163	Surface Reconstruction during Molecular Beam Epitaxial Growth of GaN (0001). MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	60
164	Morphological and compositional variations in strain-compensated InGaAsP/InGaP superlattices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1027.	1.6	19
165	Scanning tunneling microscopy observation of surface reconstruction of GaN on sapphire and 6H-SiC. Materials Research Society Symposia Proceedings, 1997, 482, 428.	0.1	1
166	Reconstructions of the GaN(0001) Surface. Physical Review Letters, 1997, 79, 3934-3937.	7.8	331
167	Nanometer-scale studies of nitride/arsenide heterostructures produced by nitrogen plasma exposure of GaAs. Journal of Electronic Materials, 1997, 26, 1342-1348.	2.2	3
168	Atomic-scale structure and electronic properties of GaN/GaAs superlattices. Applied Physics Letters, 1996, 69, 3698-3700.	3.3	52
169	Phase Separation Kinetics During Drying. Materials Research Society Symposia Proceedings, 1996, 461, 93.	0.1	1
170	Correlation of buffer strain relaxation modes with transport properties of two-dimensional electron gases. Journal of Applied Physics, 1996, 80, 6849-6854.	2.5	13
171	Unique x-ray diffraction pattern at grazing incidence from misfit dislocations in SiGe thin films. Journal of Applied Physics, 1996, 80, 89-96.	2.5	16
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